

K E J Goh

List of Publications by Year in descending order

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19
papers

335
citations

840776

11
h-index

888059

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g-index

19
all docs

19
docs citations

19
times ranked

327
citing authors

#	ARTICLE	IF	CITATIONS
1	Influence of doping density on electronic transport in degenerate Si:P δ -doped layers. Physical Review B, 2006, 73, .	3.2	62
2	Effect of encapsulation temperature on Si:P δ -doped layers. Applied Physics Letters, 2004, 85, 4953-4955.	3.3	44
3	Electron-electron interactions in highly disordered two-dimensional systems. Physical Review B, 2008, 77, .	3.2	40
4	Electronic properties of atomically abrupt tunnel junctions in silicon. Physical Review B, 2007, 75, .	3.2	31
5	The use of etched registration markers to make four-terminal electrical contacts to STM-patterned nanostructures. Nanotechnology, 2005, 16, 2446-2449.	2.6	26
6	Narrow, highly P-doped, planar wires in silicon created by scanning probe microscopy. Nanotechnology, 2007, 18, 044023.	2.6	24
7	Enhancing electron transport in Si:P delta-doped devices by rapid thermal anneal. Applied Physics Letters, 2008, 93, 142105.	3.3	13
8	Ohmic conduction of sub-10nm P-doped silicon nanowires at cryogenic temperatures. Applied Physics Letters, 2008, 92, 052101.	3.3	12
9	Effective removal of hydrogen resists used to pattern devices in silicon using scanning tunneling microscopy. Applied Physics Letters, 2005, 86, 143116.	3.3	11
10	Impact of Si growth rate on coherent electron transport in Si:P delta-doped devices. Applied Physics Letters, 2009, 95, 142104.	3.3	11
11	Patterning of sub-1 nm dangling-bond lines with atomic precision alignment on H:Si(100) surface at room temperature. Nanotechnology, 2012, 23, 275301.	2.6	11
12	Relevance of phosphorus incorporation and hydrogen removal for Si:P δ -doped layers fabricated using phosphine. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 1002-1005.	1.8	10
13	Morphology and electrical conduction of Si:P δ -doped layers on vicinal Si(001). Journal of Applied Physics, 2008, 104, 066104.	2.5	10
14	Using patterned H-resist for controlled three-dimensional growth of nanostructures. Applied Physics Letters, 2011, 98, .	3.3	9
15	Use of a scanning electron microscope to pattern large areas of a hydrogen resist for electrical contacts. Journal of Applied Physics, 2007, 102, .	2.5	8
16	Tri-Level Resistive Switching in Metal-Nanocrystal-Based $\text{Al}_2\text{O}_3/\text{SiO}_2$ Gate Stack. IEEE Transactions on Electron Devices, 2010, 57, 3001-3005.	3.0	7
17	Use of low-temperature Hall effect to measure dopant activation: Role of electron-electron interactions. Physical Review B, 2007, 76, .	3.2	6
18	Electrical properties of atomically controlled Si:P nanowires created by scanning probe microscopy. AIP Conference Proceedings, 2007, , .	0.4	0

#	ARTICLE	IF	CITATIONS
19	Study of automatic recovery on the metal nanocrystal-based Al ₂ O ₃ /SiO ₂ gate stack. Applied Physics Letters, 2011, 98, .	3.3	0